5 é / Descriptions

SOT23-3 .> / / x P 3 « | • ’ož

6 CHANNEL MOSFET in a SOT23 -3 Plastic Package.

¤ ª / Features

V_{DS}=-60V; I_D=-3A

$R_{DS(on)1}$@-10V 0 100m ¡ (Type.83m ¡)

$R_{DS(on)2}$@-4.5V 0 130m ¡ (Type.100m ¡)

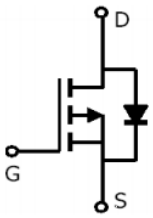
—)í D }ož HF Product.

Ð ÷ / Applications

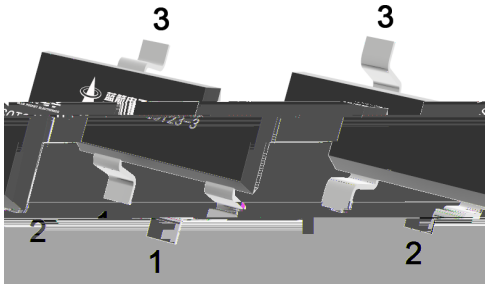
6 = 3 • ¿ ú • ¼ož

PWM application & Load switch.

Ã W] Ô · / Equivalent Circuit



• Û - æ / Pinning



PIN1 y G PIN 2 y S PIN 3 y D

, M V / Marking

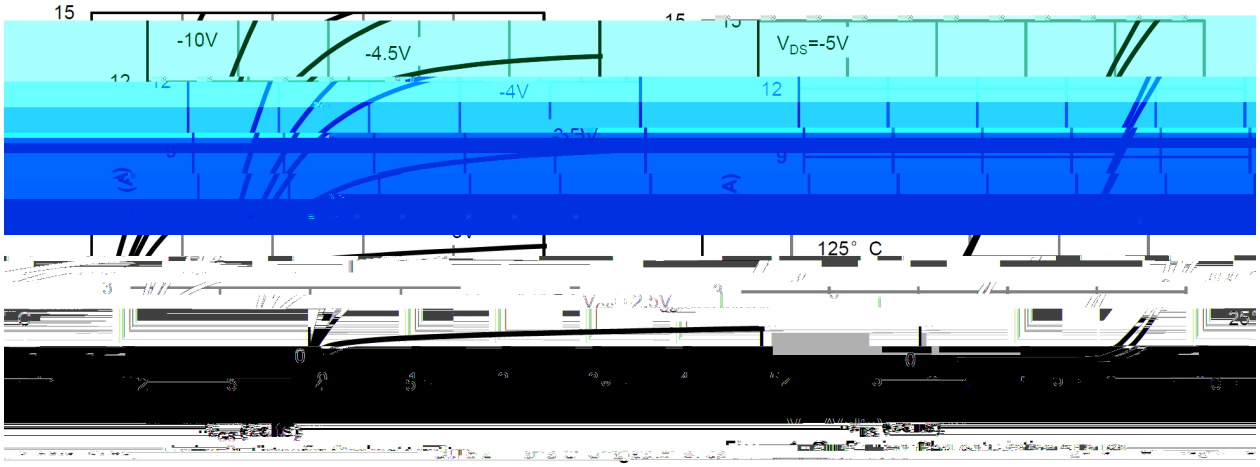
• - ~ ª ¢ož

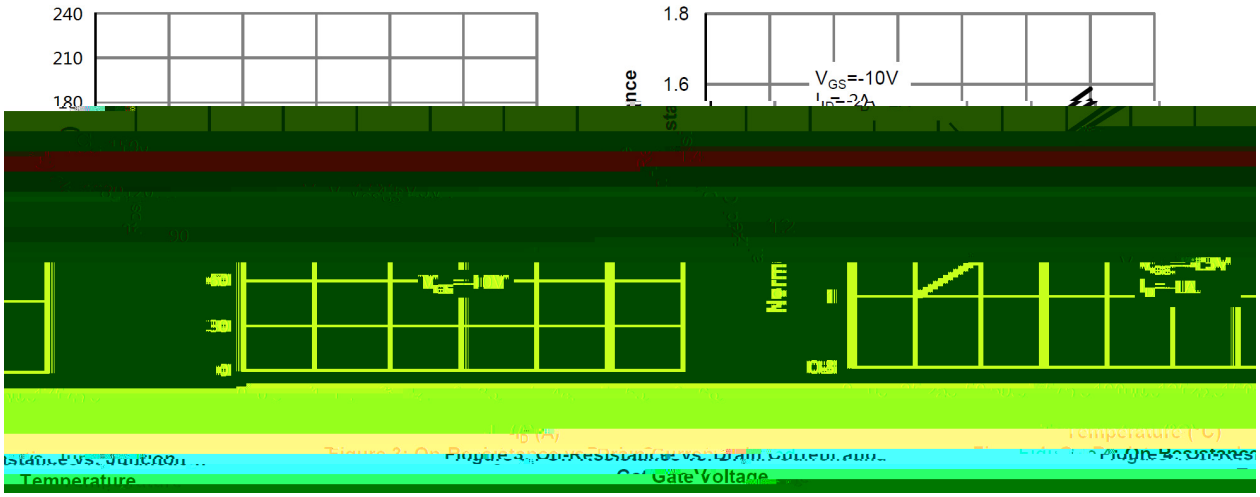
See Marking Instructions.

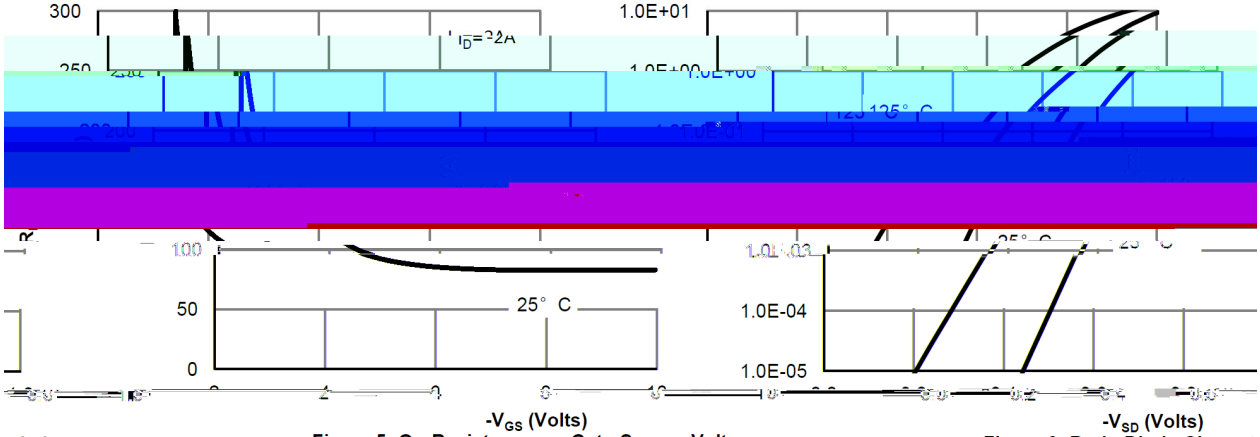
@ *f* Parameter	… Z Symbol	*f* › Rating	% y Unit
Drain–Source Voltage	V_{DSS}	-60	V
Gate–Body Lea	V_{GSS}	±20	V
Drain Cur	I_D	-3	A
Pulse rent	I_{DM}	-16	A
Po pation	D	1.4	W
O and Storage Temperature Range	TG	-55 150	
m Junction-to-Ambient		89	/W

@ *f*	Z	y ;	s	Â 4 › Min	Á º › Typ	Â Ý › Max	% y Unit
			50 A	-60	-65		V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}	I_D=-250 A	-1	-1.6	-2.5	V
Static Drain–Source On–Resistance	$R_{DS(on)}$	V_{GS}=-10V	I_D=-2A		83	100	m

Ô ? d • Ž ¢ / Electrical Characteristic Curve







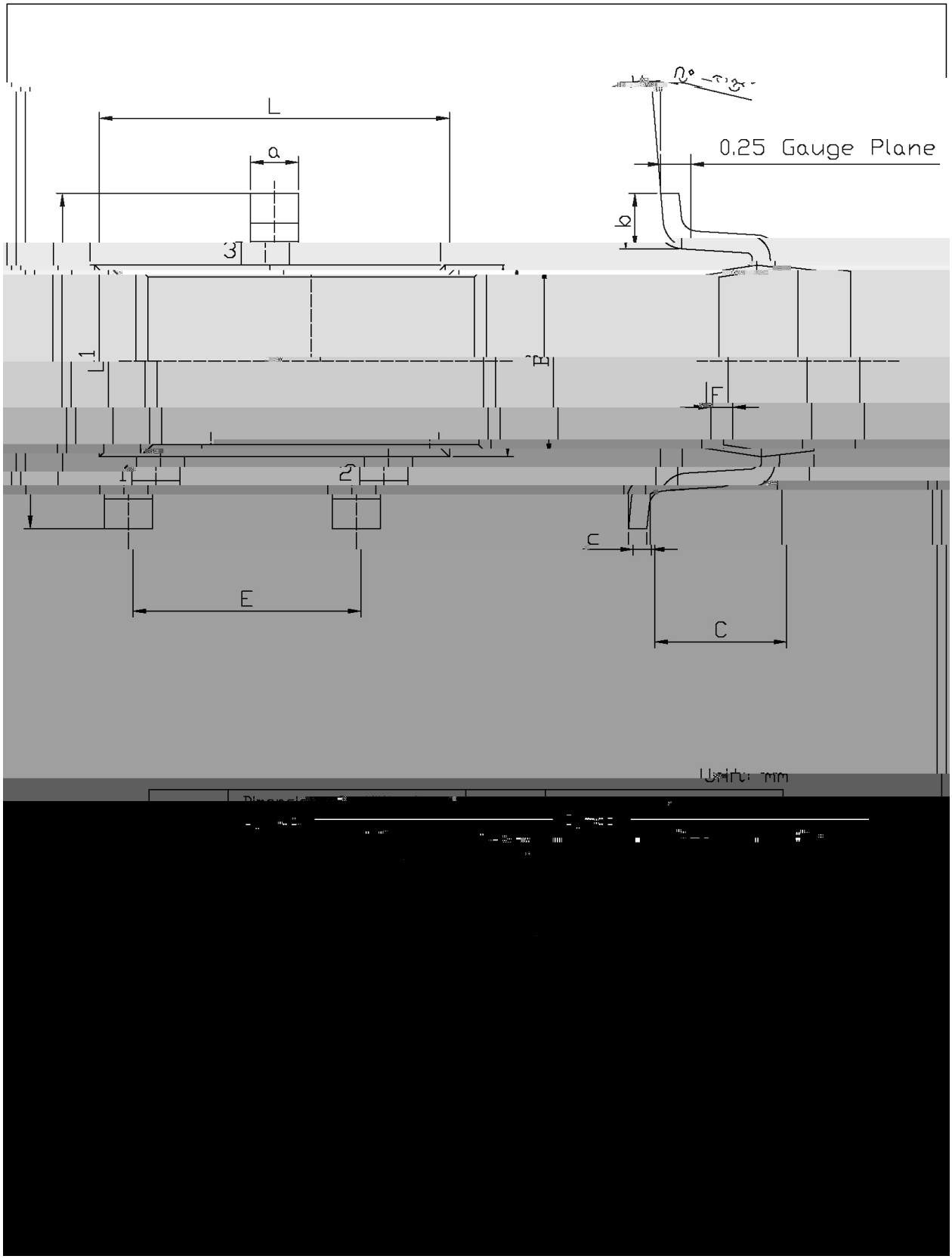
eristics

$-V_{GS}$ (Volts)
Figure 5: On-Resistance vs. Gate-Source Voltage

$-V_{SD}$ (Volts)
Figure 6: Body-Diode Charact

BRCS1C0P06MC

Ø ¤ =) ¢ / Package Dimensions



BRCS1C0P06MC

Rev.B Aug.-2025

š WD t … • Ž ¢ **(** x / **)** ***/*** : K S V K X G Z [X K 6 X U L O R K L U X / 8 8 K L R U] 9 U R J K X O T M 6

ª ¢ y

1o• Ä ½ “ † 150 ½180 - k ž • 60 ½90sec;

2o• Q › “ † 245 r5 - k ž • 4 Ò 5 r0.5sec;

3o•D N ò i Ò 0 , † 2 ½10 - /sec.

Note:

1.Preheating:150~180 - , Time:60~90sec.

2.Peak Temp.:245 r5 - , Duration:5 r0.5sec.

3. Cooling Speed: 2~10 - /sec.

ÂD /Cã p ¯ »] / Resistance to Soldering Heat Test Conditions

“ † y 260 r5 - ž • y 10 r1 sec. Temp.:260±5 Time:10±1 sec

G P á / Packaging SPEC.

2 & x / REEL

Package Type 7>û ˜ E	Units ;>û ¦H					Dimension ;>û p . (unit Æmm³)		
	Units/Reel / --	Reels/Inner Box -- /-	Units/Inner Box /-	Inner Boxes/Outer Box - /1ç	Units/Outer Box /1ç	Reel	Inner Box×	Outer Box1ç ÂD4€ ïSv5v7T L ”„